

Title (en)

HIGH FREQUENCY TRANSISTOR POWER AMPLIFIER

Publication

**EP 0450316 A3 19911113 (DE)**

Application

**EP 91103166 A 19910302**

Priority

DE 4010409 A 19900331

Abstract (en)

[origin: EP0450316A2] In a high-frequency transistor power amplifier having several power transistors arranged in a circle, the input terminals of the transistors are connected via separate input matching circuits and a distributor circuit to a common input whilst the output terminals of the power transistors are directly combined in a common output terminal without interconnecting matching circuits, which is connected to a single output matching circuit common to all power transistors.

IPC 1-7

**H03F 3/60**

IPC 8 full level

**H03F 3/60** (2006.01)

CPC (source: EP US)

**H03F 3/602** (2013.01 - EP US)

Citation (search report)

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- [Y] EP 0275587 A1 19880727 - RADIOTECHNIQUE IND & COMM [FR], et al
- [YD] US 4641107 A 19870203 - KALOKITIS DAVID [US]
- [AD] EP 0085393 A1 19830810 - SIEMENS AG [DE]
- [A] NEC RESEARCH AND DEVELOPMENT, no. 48, January 1978, TOKYO, JP; pages 53 - 59; (Y. SAITO ET AL.): 'A 4 GHZ HIGH POWER, HIGH GAIN TRANSISTOR AMPLIFIER USING INTERNAL MATCHING TECHNOLOGY AND NEGATIVE RESISTANCE AMPLIFIER TECHNOLOGY'

Cited by

EP0493081A3

Designated contracting state (EPC)

DE FR GB IT NL

DOCDB simple family (publication)

**EP 0450316 A2 19911009; EP 0450316 A3 19911113; DE 4010409 A1 19911002; US 5121083 A 19920609**

DOCDB simple family (application)

**EP 91103166 A 19910302; DE 4010409 A 19900331; US 67551591 A 19910327**